

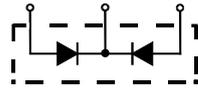
HUR2060CTA1

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

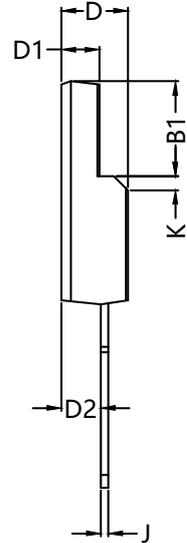
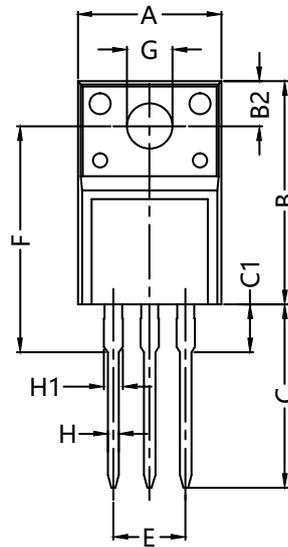


Dimensions TO-220F

1(A1) 2(K) 3(A2)



A1 = Anode 1
A2 = Anode 2
K = Cathode



	V _{RSM} V	V _{RRM} V
HUR2060CTA1	220	200

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test Conditions	Values	Unit
V _R	Maximum D.C. Reverse Voltage		600	V
V _{RRM}	Maximum Repetitive Reverse Voltage		600	V
I _{F(AV)}	Average Forward Current	T _C =110°C, Per Diode	10	A
		T _C =110°C, Per Package	20	A
I _{F(RMS)}	RMS Forward Current	T _C =110°C, Per Diode	14	A
I _{FSM}	Non-Repetitive Surge Forward Current	T _J =45°C, t=10ms, 50Hz, Sine	150	A
P _D	Power Dissipation		80	W
T _J	Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature Range		-40 to +150	°C
R _{θJC}	Thermal Resistance	Junction-to-Case	2.23	°C/W
V _{ISO}	1min / 1 sec	Terminal-to-Case	2000/2500	VAC
Weight			2	g

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$T_C=25^\circ\text{C}$ unless otherwise specified

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	$V_R=600\text{V}$	--	--	10	μA
		$V_R=600\text{V}, T_J=125^\circ\text{C}$	--	--	10	mA
V_F	Forward Voltage	$I_F=10\text{A}$	--	1.40	1.60	V
		$I_F=10\text{A}, T_J=125^\circ\text{C}$	--	--	1.25	V
t_{rr}	Reverse Recovery Time	$I_F=1\text{A}, V_R=30\text{V}, di_F/dt=-200\text{A}/\mu\text{s}$	--	40	55	ns
t_{rr}	Reverse Recovery Time	$V_R=100\text{V}, I_F=10\text{A}$	--	60	90	ns
I_{RRM}	Max. Reverse Recovery Current	$di_F/dt=-200\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$	--	2.1	--	A
t_{rr}	Reverse Recovery Time	$T_J=100^\circ\text{C}, V_R=100\text{V}, I_F=10\text{A}, di_F/dt=-200\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$	--	95	115	ns
I_{RRM}	Max. Reverse Recovery Current	$dt=-200\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$	--	5	--	A

FEATURES

- * International standard package **TO-220F**
- * Planar passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM} -values
- * Soft recovery behaviour
- * RoHS compliant

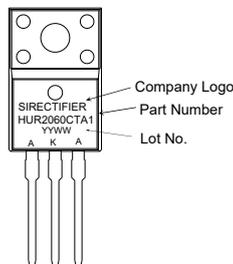
APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating and melting
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * High reliability circuit operation
- * Low voltage peaks for reduced protection circuits
- * Low noise switching
- * Low losses
- * Operating at lower temperature or space saving by reduced cooling

Marking



Ordering Information

Part Number	Package	Shipping	Marking Code
HUR2060CTA1	TO-220F	50pcs / Tube	HUR2060CTA1

Sirectifier[®]

HUR2060CTA1

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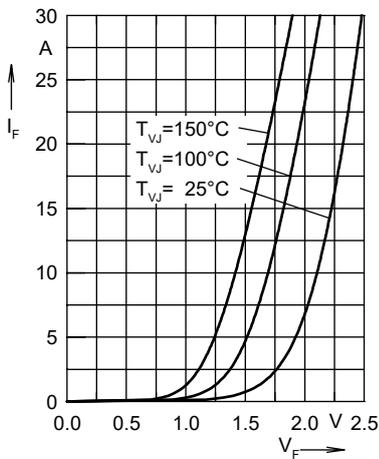


Fig. 1 Forward current I_F versus V_F

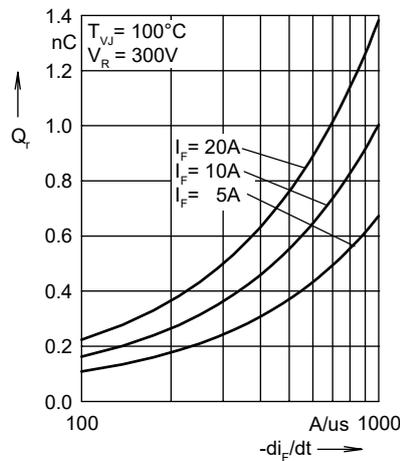


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

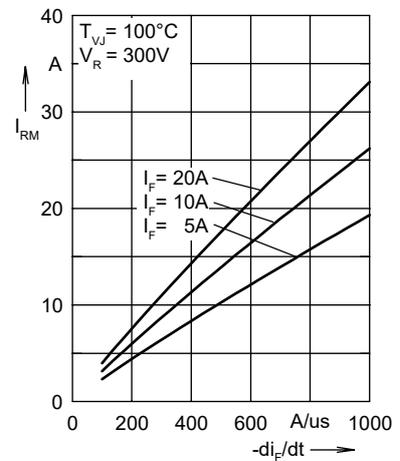


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

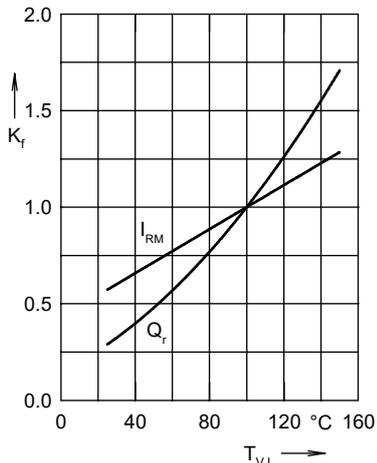


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

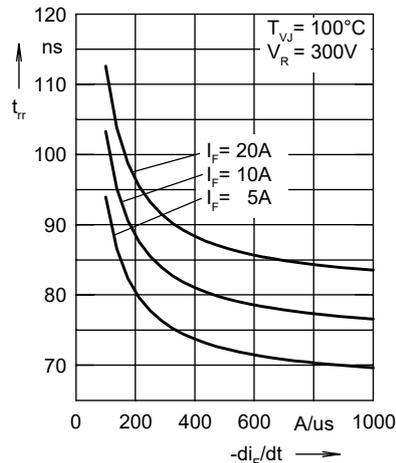


Fig. 5 Recovery time t_{tr} versus $-di_F/dt$

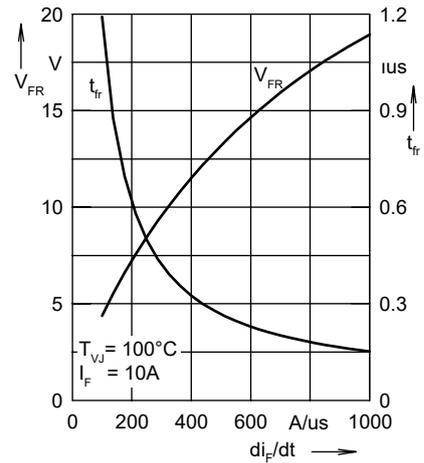


Fig. 6 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

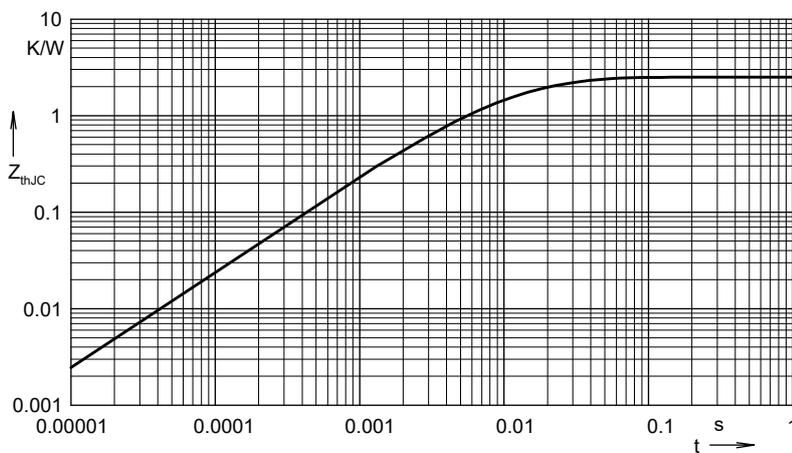


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.449	0.0052
2	0.5578	0.0003
3	0.4931	0.0169